



安徽富信半導體科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD

US3A THRU US3M

3.0 AMP SURFACE MOUNT HIGH EFFICIENCY RECTIFIERS



FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.093 grams

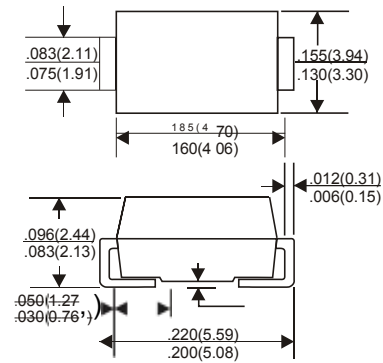
VOLTAGE RANGE

50 to 1000 Volts

CURRENT

3.0 Ampere

DO-214AA(SMB)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 °C ambient temperature unless otherwise specified.
 Single phase half wave, 60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

TYPE NUMBER	US3A	US3B	US3D	US3E	US3G	US3J	US3K	US3M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta=55 C	3.0								A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	100								A
Maximum Instantaneous Forward Voltage at 3.0A	1.0		1.3		1.85				V
Maximum DC Reverse Current Ta=25°C	10								µA
at Rated DC Blocking Voltage Ta=100 C	200								µA
Maximum Reverse Recovery Time (Note 1)	50				75				nS
Typical Junction Capacitance (Note 2)	75								pF
Operating and Storage Temperature Range Tj , Tstg	-65—+150								°C

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (US3A THRU US3M)

FIG. 1-TYPICAL FORWARD CHARACTERISTICS

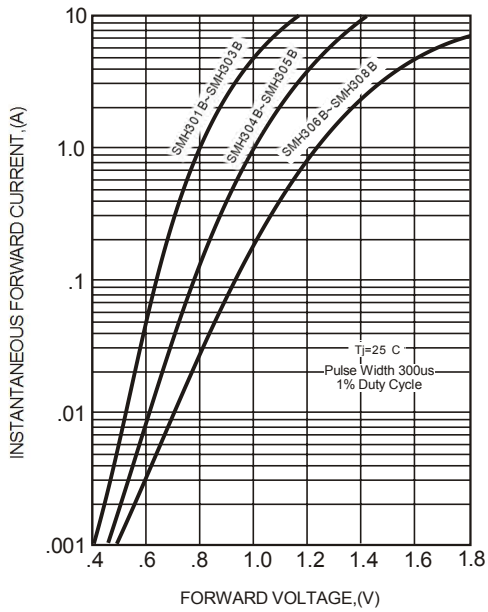


FIG. 2-TYPICAL FORWARD CURRENT DERATING CURVE

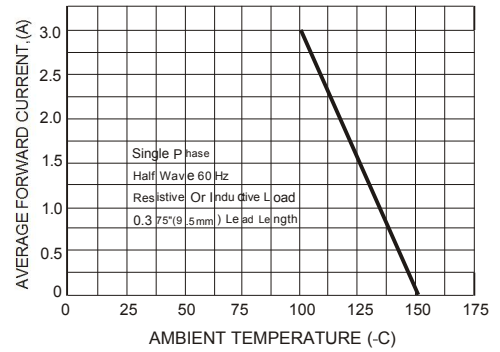


FIG. 4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

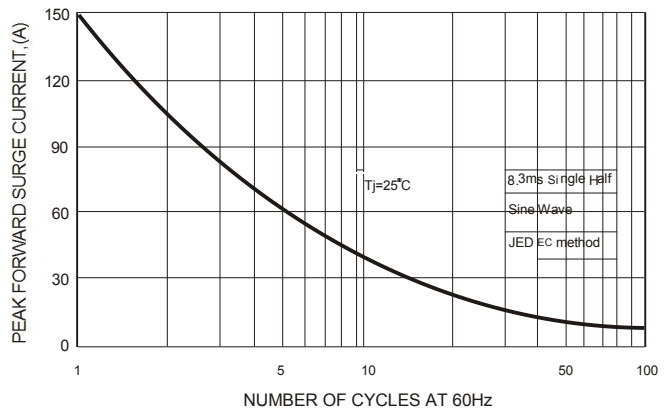
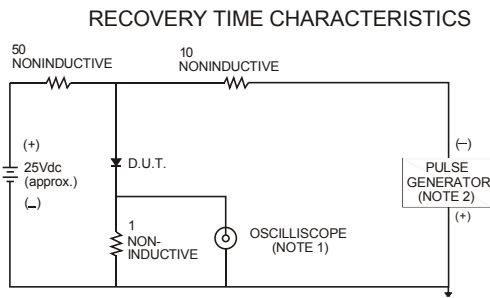


FIG. 3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

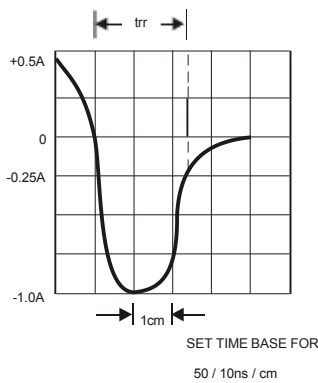
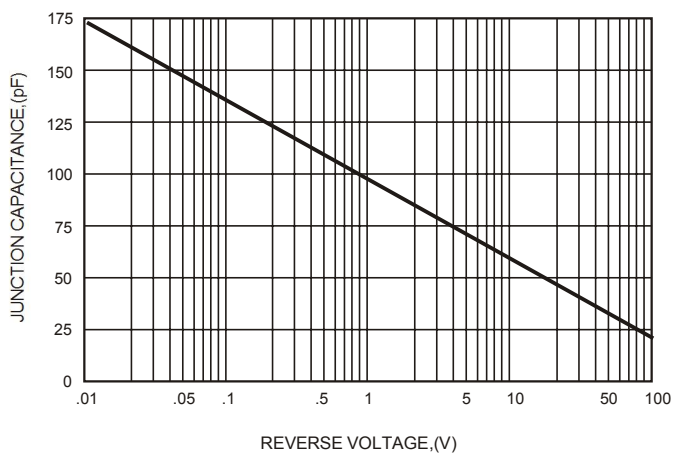


FIG. 5-TYPICAL JUNCTION CAPACITANCE



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